

Vishay Siliconix

3-Ω, **235-MHz Bandwidth**, Dual SPDT Analog Switch

DESCRIPTION

The DG2515, DG2516 are low-voltage dual single-pole/ double-throw monolithic CMOS analog switches. Designed to operate from 1.8 V to 5.5 V power supply, the DG2515, DG2516 achieves a bandwidth of 235 MHz while providing low on-resistance (3 Ω), excellent on-resistance matching (0.2Ω) and flatness (1Ω) over the entire signal range.

The DG2515. DG2516 offers the advantage of high linearity that reduces signal distortion, making ideal for audio, video, and USB signal routing applications. Additionally, the DG2515, DG2516 are 1.6 V logic compatible within the full operation voltage range.

Built on Vishay Siliconix's proprietary sub-micron highdensity process, the DG2515, DG2516 brings low power consumption at the same time as reduces PCB spacing with the MSOP10 package.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For analog switching products manufactured with 100 % matte tin device termination, the lead (Pb)-free "- E3" suffix is being used as a designator.

FEATURES

- 1.8 V to 5.5 V single supply operation
- Low R_{ON}: 3 Ω at 4.2 V
- 235 MHz, 3 dB bandwidth
- Low off-isolation. 51 dB at 10 MHz
- + 1.6 V logic compatible

BENEFITS

- High linearity
- Low power consumption
- High bandwidth
- Full rail signal swing range

APPLICATIONS

- USB/UART signal switching
- Audio/video switching
- Cellular phone
- Media players
- Modems
- Hard drives
- PCMCIA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION









TRUTH TABLE						
Logic	NC1 and NC2	NO1 and NO2				
0	ON	OFF				
1	OFF	ON				

ORDERING IN	ORDERING INFORMATION					
Temp Range	Package	Part Number				
- 40 °C to 85 °C	MSOP-10	DG2515DQ-T1-E3				
- 40 C 10 65 C	WIGOF-10	DG2516DQ-T1-E3				



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ABSOLUTE MAXIMUM RATINGS						
Parameter	Limit	Unit				
Reference to GND						
V+		- 0.3 to + 6	N			
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	V			
Continuous Current (Any terminal)	± 50	mA				
Peak Current (Pulsed at 1 ms, 10 % Du	ty Cycle)	± 200	- IIIA			
Storage Temperature (D Suffix)		- 65 to 150	°C			
Power Dissipation (Packages) ^b	MSOP-10 ^c	320	mW			

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. All leads welded or soldered to PC board.

c. Derate 4.0 mW/°C above 70 °C.

SPECIFICATIONS V+	= 3 V								
	Test Conditions Otherwise Unless Specified - 40		Limits 0 °C to 85 °C						
Parameter	Symbol	$V + = 3 V, \pm 10 \%, V_{IN} = 0.$		Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit	
Analog Switch							1		
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}			Full	0		V+	V	
On-Resistance	R _{ON}	V+ = 2.7 V, V _{COM} = I _{NO/NC} = 10 mA	1.5 V	Room Full		3.2	4.5 5.0		
R _{ON} Flatness	R _{ON} Flatness	$V_{+} = 2.7 V, V_{COM} = 1$ $I_{NO/NC} = 10 mA$.5, 2 V	Room Full		1.0	1.4 16	Ω	
R _{ON} Match Between Channels	ΔR_{ON}	V+ = 2.7 V, V _{COM} = I _{NO/NC} = 10 mA	1.5 V	Room Full		0.1	0.3 0.4		
Switch Off Leakage Current ^f	I _{NO(off),} I _{NC(off)}	V+ = 3.6 V, V _{NO} , V _{NC} = V _{COM} = 3 V/0.3	0.3 V/3 V	Room Full	- 1 - 10		1 10		
Switch On Leakage Current	I _{COM(off)}	V _{COM} = 3 V/0.3	V	Room Full	- 1 - 10		1 10	nA	
Channel-On Leakage Current ^f	I _{COM(on)}	$V + = 3.6 V, V_{NO}, V_{NC} = V_{CO}$	_M = 0.3 V/3 V	Room Full	- 1 - 10		1 10		
Digital Control	1						1	1	
Input High Voltage ^d	V _{INH}			Full	1.4			Ň	
Input Low Voltage	V _{INL}			Full			0.5	V	
Input Capacitance	C _{in}			Full		12		pF	
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V+		Full	1		1	μA	
Dynamic Characteristics		L							
Turn-On Time	t _{ON}	V+ = 2.7 V, V _{NO} or V _{NC} R _L = 300 Ω, C _L = 3	<u>_</u> = 1.5 V	Room Full		30	70 100		
Turn-Off Time	t _{OFF}	R _L = 300 Ω, C _L = 3	5 pF	Room Full		25	50 70	ns	
Break-Before-Make Time	t _d	$V_{\rm NO} \text{ or } V_{\rm NC} = 1.5 \text{ V}, \text{ R}_{\rm L} = 300$	Ω, C_L = 35 pF	Full	1				
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R	_{GEN} = 0 Ω	Room		24		рС	
- 3 dB Bandwidth	BW	0 dBm, C _L = 5 pF, R _L	= 50 Ω	Room		235		MHz	
Off-Isolation ^d	OIRR	R ₁ = 50 Ω, C ₁ = 5 pF	f = 1 MHz	Room		- 71			
Off-Isolation"	OINN	n_ = 30 sz, 0_ = 3 pr	f = 10 MHz	Room		- 51		dB	
Crosstalk ^d	X _{TALK}	$R_1 = 50 \Omega, C_1 = 5 pF$	f = 1 MHz	Room		- 74		uD	
Orosstaik			f = 10 MHz	Room		- 52			
N _O , N _C Off Capacitance ^d	C _{NO(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		17		– pF	
	C _{NC(off)}			Room		17			
	C _{NO(on)}			Room		40			
	C _{NC(on)}			Room		40			
Power Supply	1			1			1	1	
Power Supply Current	l+	$V_{IN} = 0 \text{ or } V+$		Full		0.01	1.0	μΑ	

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SPECIFICATIONS V+	= 5 V	1						-
		Test Conditions Otherwise Unless Specified			Limits - 40 °C to 85 °C			
Parameter	Symbol	V+ = 5 V, ± 10 %, V _{IN} = 0	.8 or 2.0 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch		•						
Analog Signal Range ^d	V _{NO} , V _{NC} , V _{COM}			Full	0		V+	v
On-Resistance	R _{ON}	$V_{+} = 4.2 V, V_{COM} = 3.5 V, I_{N}$	_{IO/NC} = 10 mA	Room Full		3	4.0 4.3	
R _{ON} Flatness	R _{ON} Flatness	$V_{+} = 4.2 V, V_{COM} = 1,$ $I_{NO/NC} = 10 mA$		Room Full		1.1	1.4 1.6	Ω
R _{ON} Match Between Channels	ΔR_{ON}	$V_{+} = 4.2 \text{ V}, V_{COM} = 3.5 \text{ V}, I_{N}$	_{IO/NC} = 10 mA	Room Full		0.1	0.3 0.4	
Switch Off Leakage Current	I _{NO(off)} , I _{NC(off)}	V+ = 5.5 V		Room Full	- 1 - 10		1 10	
Switch On Leakage Sunon	I _{COM(off)}	$V_{\rm NO}, V_{\rm NC} = 1 \text{ V}/4.5 \text{ V}, V_{\rm COI}$	_M = 4.5 V/1 V	Room Full	- 1 - 10		1 10	nA
Channel-On Leakage Current	I _{COM(on)}	$V + = 5.5 V, V_{NO}, V_{NC} = V_{CC}$	_{OM} = 1 V/4.5 V	Room Full	- 1 - 10		1 10	1
Digital Control		•					•	
Input High Voltage ^d	V _{INH}			Full	2.0			v
Input Low Voltage	V _{INL}			Full			0.8	v
Input Capacitance	C _{in}			Full		12		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 V or V-	F	Full	1		1	μA
Dynamic Characteristics		•						
Turn-On Time	t _{ON}	V+ = 4.2 V, V _{NO} or V _N		Room Full		25	50 70	
Turn-Off Time	t _{OFF}	R _L = 300 Ω, C _L = 3		Room Full		20	40 50	ns
Break-Before-Make Time	t _d	V_{NO} or V_{NC} = 3 V, R_L = 300	Ω, C _L = 35 pF	Full	1			
Charge Injection ^d	Q _{INJ}	C _L = 1 nF, V _{GEN} = 0 V, R	G _{EN} = 0 Ω	Room		49		рС
- 3 dB Bandwidth	BW	0 dBm, $C_L = 5 \text{ pF}$, R_L	= 50 Ω	Room		235		MHz
Off-Isolation ^d	OIRR	$R_L = 50 \Omega$, $C_L = 5 pF$	f = 1 MHz f = 10 MHz	Room Room		- 71 - 51		dP
Crosstalk ^d	X _{TALK}	$R_L = 50 $ Ω, $C_L = 5 $ pF	f = 1 MHz f = 10 MHz	Room Room		- 74 - 52		dB
	C _{NO(off)}		Room		17		pF	
Source Off Capacitance ^d	C _{NC(off)}	V _{IN} = 0 or V+, f = 1 MHz		Room		17		
d i o o i d	C _{NO(on)}	v _{IN} = 0 01 v+, 1 = 1		Room		40		pr
Channel-On Capacitance ^d	C _{NC(on)}			Room		40		
Power Supply								
Power Supply Range	V+				1.8		5.5	V
Power Supply Current	l+	V _{IN} = 0 or V+		Full		0.01	1.0	μA

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Guarantee by design, nor subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

/ISHA

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10M

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Leakage Current vs. Temperature

Document Number: 73453 S-82589-Rev. B, 27-Oct-08

Leakage vs. Analog Voltage



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



V+ - Supply Voltage (V) Switching Threshold vs. Supply Voltage

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TEST CIRCUITS





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Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.







C_L (includes fixture and stray capacitance)







IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection



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TEST CIRCUITS







Figure 5. Channel Off/On Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73453.



Package Information Vishay Siliconix

MSOP: 10-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)







NOTES:

/4.\

/5.\

1. Die thickness allowable is 0.203 ± 0.0127 .

2. Dimensioning and tolerances per ANSI.Y14.5M-1994.

/3. Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane _-H- , mold flash or protrusions shall not exceed 0.15 mm per side.

Dimension is the length of terminal for soldering to a substrate.

Terminal positions are shown for reference only.

6. Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.

The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".

/8. Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.

9. Controlling dimension: millimeters.

10. This part is compliant with JEDEC registration MO-187, variation AA and BA.

11 Datums -A- and -B- to be determined Datum plane -H-.

12 Exposed pad area in bottom side is the same as teh leadframe pad size.











N = 10L

	М	LLIMETE	RS	
Dim	Min	Nom	Max	Note
Α	-	-	1.10	
A ₁	0.05	0.10	0.15	
A ₂	0.75	0.85	0.95	
b	0.17	-	0.27	8
b ₁	0.17	0.20	0.23	8
С	0.13	-	0.23	
c ₁	0.13	0.15	0.18	
D		3.00 BSC		3
Е		4.90 BSC		
E ₁	2.90	3.00	3.10	3
е		0.50 BSC		
е ₁		2.00 BSC		
L	0.40	0.55	0.70	4
Ν		5		
x	0°	4°	6°	
CN: T-02 DWG: 58	2080—Rev. 0 67	C, 15-Jul-02		



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